MANUFACTURE OF SEMICONDUCTOR DEVICE

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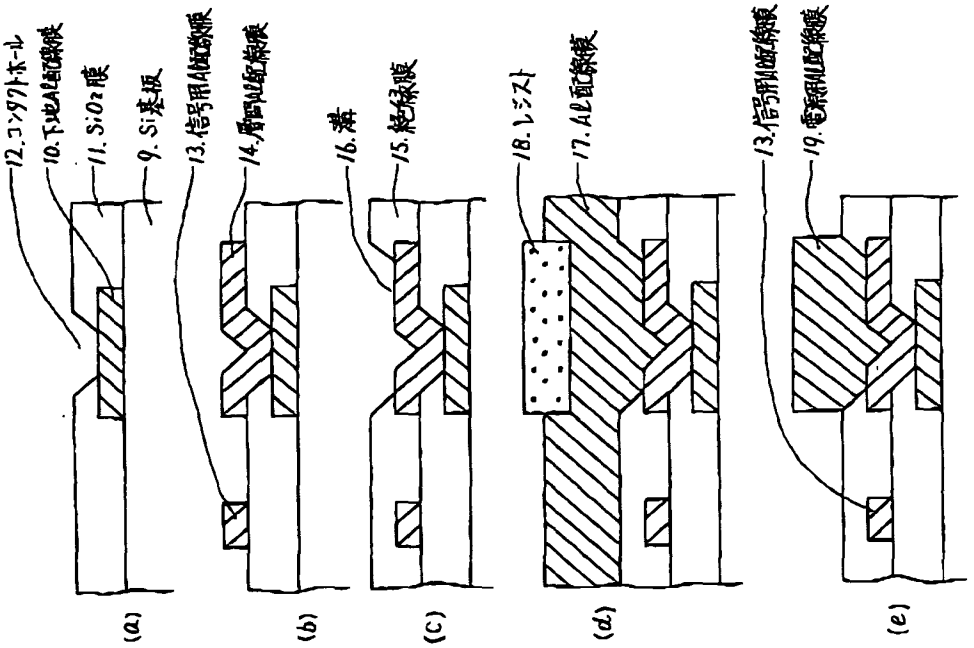
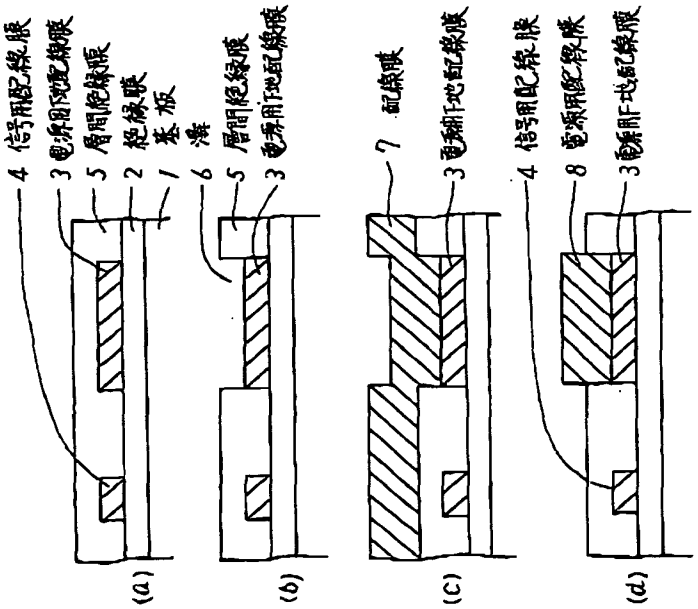
Equivalents:

Abstract

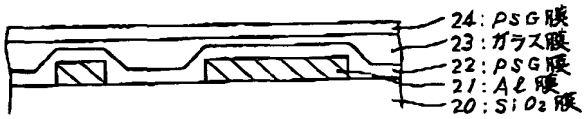
PURPOSE:To reduce a difference in level of a multilayer wiring insulating layer, to increase an effect of a flattening operation and to enhance a coverage of a protective film by a method wherein a substratum wiring film for power- supply use and a wiring film for signal use are formed on an insulating film which has been applied to a substrate.
CONSTITUTION:A substratum wiring film 3 and a wiring film 4 for signal use are formed on a s miconductor-device substrate 1 where an element-wiring operation has been finished; after that, an interlayer insulating film 5 is coated on it. Then, only the interlayer insulating film 5 on the substratum wiring film 3 is removed; a groove 6 whose pattern is identical to a power-supply wiring pattern is formed in the interlayer insulating film 5 by using the substratum wiring film 3 as a stopper; a wiring film 7 is deposited. In addition, the wiring film 7 in a part other than the groove 6 is removed; a wiring film 8 for power- supply use is completed. Thereby, it is possible to reduce a depth portion of the groove at a difference in level by the thick power-supply wiring part. A coverage of a protective film is made good; reliability of a semiconductor device is enhanced.



本発明の一実施例の工程順模式断面図
第2図

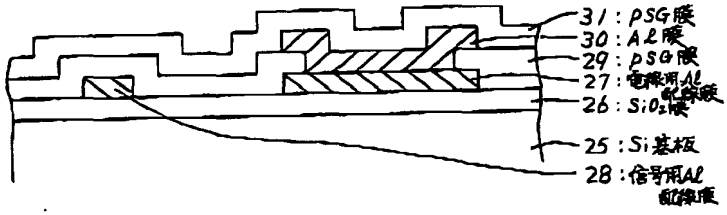


本発明の原理説明図
第1図



一実施例中の絶縁膜平坦化の説明図

第3図



従来例の模式 断面図

第4図